Quad 3-State Noninverting Buffer with LSTTL Compatible Inputs

High-Performance Silicon-Gate CMOS

The MC74HCT125A is identical in pinout to the LS125. The device inputs are compatible with standard CMOS and LSTTL outputs.

The MC74HCT125A noninverting buffer is designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. The devices have four separate output enables that are active-low.

Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the JEDEC Standard No. 7A Requirements
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb–Free Devices

PIN ASSIGNMENT

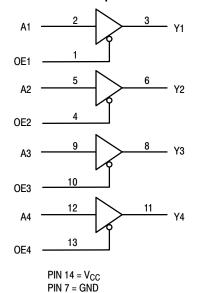
| 0E1 [| 1 ● | 14 | v _{cc} |
|-------|-----|----|-----------------|
| A1 [| 2 | 13 | 0E4 |
| Y1 [| 3 | 12 |] A4 |
| OE2 [| 4 | 11 |] Y4 |
| A2 [| 5 | 10 | 0E3 |
| Y2 [| 6 | 9 | _ A3 |
| GND [| 7 | 8 |] Y3 |
| | | | J |

FUNCTION TABLE

| HCT125A | | | | | |
|---------|------|--------|--|--|--|
| Inp | outs | Output | | | |
| Α | OE | Υ | | | |
| Н | L | Н | | | |
| L | L | L | | | |
| Χ | Н | Z | | | |

LOGIC DIAGRAM

Active-Low Output Enables





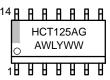
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MARKING DIAGRAMS



SOIC-14 D SUFFIX CASE 751A





TSSOP-14 DT SUFFIX CASE 948G



A = Assembly Location

L, WL = Wafer Lot Y, YY = Year

W, WW = Work Week
G = Pb-Free Package
• Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|------------------|---|--------------------------|------|
| V _{CC} | DC Supply Voltage (Referenced to GND) | - 0.5 to + 7.0 | V |
| V _{in} | DC Input Voltage (Referenced to GND) | -0.5 to $V_{CC} + 0.5$ | V |
| V _{out} | DC Output Voltage (Referenced to GND) | -0.5 to $V_{CC} + 0.5$ | V |
| l _{in} | DC Input Current, per Pin | ± 20 | mA |
| I _{out} | DC Output Current, per Pin | ± 35 | mA |
| I _{CC} | DC Supply Current, V _{CC} and GND Pins | ± 75 | mA |
| P _D | Power Dissipation in Still Air SOIC Package† TSSOP Package† | 500 450 | mW |
| T _{stg} | Storage Temperature | - 65 to + 150 | °C |
| TL | Lead Temperature, 1 mm from Case for 10 Seconds (SOIC or TSSOP Package) | 260 | °C |

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — SOIC Package: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit | |
|------------------------------------|---|--|-------------|--------------------|----|
| V _{CC} | DC Supply Voltage (Referenced to GND) | | 2.0 | 6.0 | V |
| V _{in} , V _{out} | DC Input Voltage, Output Voltage (Referenced to GND) | | 0 | V _{CC} | V |
| T _A | Operating Temperature, All Package Types | | - 55 | + 125 | °C |
| t _r , t _f | Input Rise and Fall Time (Figure 1) | $V_{CC} = 2.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$ | 0 0 0 | 1000 500 400 | ns |

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

| | | | | Gu | aranteed Li | mit | |
|-----------------|--|---|----------------------|--------------------|--------------------|-------------------|------|
| Symbol | Parameter | Test Conditions | V _{CC} V | – 55 to 25°C | ≤ 85°C | ≤ 125°C | Unit |
| V _{IH} | Minimum High-Level Input Voltage | $V_{\text{out}} = V_{\text{CC}} - 0.1 \text{ V}$ $ I_{\text{out}} \le 20 \mu\text{A}$ | 4.5 to 5.5 | 2.0 | 2.0 | 2.0 | V |
| V _{IL} | Maximum Low–Level Input Voltage | $V_{out} = 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$ | 4.5 to 5.5 | 0.8 | 0.8 | 0.8 | V |
| V _{OH} | Minimum High-Level Output Voltage | $V_{in} = V_{IH}$ $ I_{out} \le 20 \mu A$ | 4.5 5.5 4.5 | 4.4 5.4 3.98 | 4.4 5.4 | 4.4 5.4 3.7 | V |
| V _{OL} | Maximum Low–Level Output Voltage | $\begin{aligned} &V_{in} = V_{IH} & & I_{out} \leq 6.0 \text{ mA} \\ &V_{in} = V_{IL} & & \\ & I_{out} \leq 20 \mu\text{A} \end{aligned}$ | 4.5 5.5 | 0.1 0.1 | 3.84 0.1 0.1 | 0.1 0.1 | V |
| l _{in} | Maximum Input Leakage Current | $V_{in} = V_{IL}$ $ I_{out} \le 6.0 \text{ mA}$ $V_{in} = V_{CC} \text{ or GND}$ | 4.5 5.5 | 0.26 ± 0.1 | 0.33 ± 1.0 | 0.4 ± 1.0 | μΑ |
| I _{OZ} | Maximum Three–State Leakage Current | Output in High-Impedance State $V_{in} = V_{IL}$ or V_{IH} $V_{out} = V_{CC}$ or GND | 5.5 | ± 0.5 | ± 5.0 | ± 10 | μΑ |
| Icc | Maximum Quiescent Supply Current (per Package) | $V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$ | 5.5 | 4.0 | 40 | 160 | μΑ |

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6.0 ns, V_{CC} = 5.0 V \pm 10%)

| | | | Guaranteed Limit | | | |
|--|---|-----------------|------------------|------------------------|----------------------|------|
| Symbol | Parameter | V _{CC} | – 55 to 25°C | ≤ 85°C | ≤ 125°C | Unit |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, Input A to Output Y (Figures 1 and 3) | 5.0 | 18 | 23 | 27 | ns |
| t _{PLZ} , t _{PHZ} | Maximum Propagation Delay, Output Enable to Y (Figures 2 and 4) | 5.0 | 24 | 30 | 36 | ns |
| t _{PZL} , t _{PZH} | Maximum Propagation Delay, Output Enable to Y (Figures 2 and 4) | 5.0 | 18 | 23 | 27 | ns |
| t _{TLH} , t _{THL} | Maximum Output Transition Time, Any Output (Figures 1 and 3) | 5.0 | 12 | 15 | 18 | ns |
| C _{in} | Maximum Input Capacitance | - | 10 | 10 | 10 | pF |
| C _{out} | Maximum 3-State Output Capacitance (Output in High-Impedance State) | _ | 15 | 15 | 15 | pF |
| | | | Typical | @ 25°C, V _C | _C = 5.0 V | |
| _ | | | 1 | 00 | | _ |

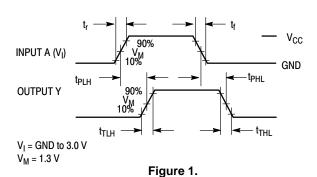
ORDERING INFORMATION

| Device | Package | Shipping [†] |
|-------------------|-----------------------|-----------------------|
| MC74HCT125ADG | | 55 Units / Rail |
| MC74HCT125ADR2G | SOIC-14 (Pb-Free) | 2500 / Tape & Reel |
| NLV74HCT125ADR2G* | (1 11) | 2500 / Tape & Reel |
| MC74HCT125ADTG | | 96 Units / Rail |
| MC74HCT125ADTR2G | TSSOP-14 (Pb-Free) | 2500 / Tape & Reel |
| NLVHCT125ADTR2G* | , , , | 2500 / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

SWITCHING WAVEFORMS



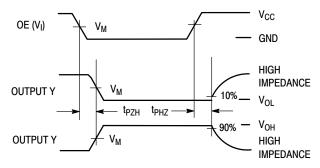
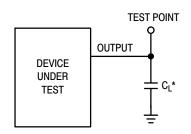
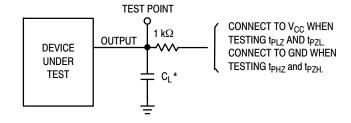


Figure 2.



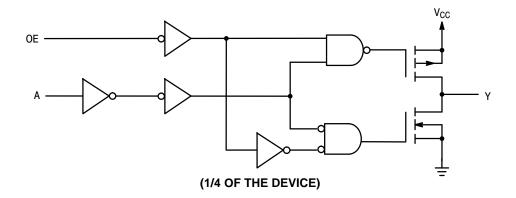


*Includes all probe and jig capacitance

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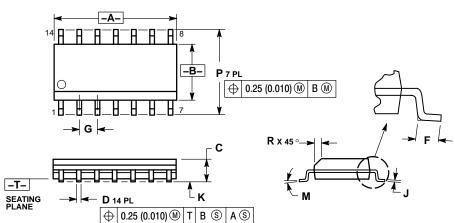
Figure 3. Test Circuit

Figure 4. Test Circuit



PACKAGE DIMENSIONS

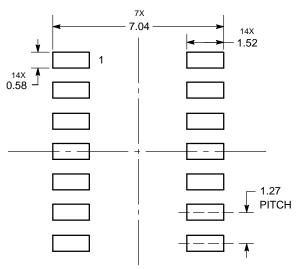
SOIC-14 CASE 751A-03 **ISSUE J**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- 4. MAXIMUM MOLD PROTRUSION 0.15 (0.00 PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

| | MILLIMETERS | | INC | HES |
|-----|-------------|------|-----------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 8.55 | 8.75 | 0.337 | 0.344 |
| В | 3.80 | 4.00 | 0.150 | 0.157 |
| С | 1.35 | 1.75 | 0.054 | 0.068 |
| D | 0.35 | 0.49 | 0.014 | 0.019 |
| F | 0.40 | 1.25 | 0.016 | 0.049 |
| G | 1.27 BSC | | 0.050 BSC | |
| J | 0.19 | 0.25 | 0.008 | 0.009 |
| K | 0.10 | 0.25 | 0.004 | 0.009 |
| М | 0 ° | 7° | 0 ° | 7° |
| Р | 5.80 | 6.20 | 0.228 | 0.244 |
| R | 0.25 | 0.50 | 0.010 | 0.019 |

SOLDERING FOOTPRINT*

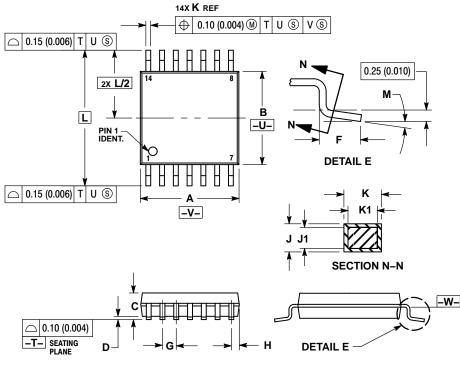


DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSSOP-14 CASE 948G ISSUE B



NOTES:

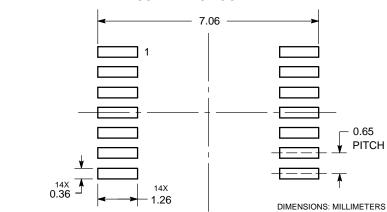
- DIMENSIONING AND TOLERANCING PER
 ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD
 FLASH, PROTRUSIONS OR GATE BURRS.
 MOLD FLASH OR GATE BURRS SHALL NOT
 EXCEPD 15 (10 00) PER SIDE
- EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE
 INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
 NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE
- 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

| | MILLIN | IETERS | INC | HES | | |
|-----|--------|--------|-----------|-------|--|--|
| DIM | MIN | MAX | MIN | MAX | | |
| Α | 4.90 | 5.10 | 0.193 | 0.200 | | |
| В | 4.30 | 4.50 | 0.169 | 0.177 | | |
| С | | 1.20 | | 0.047 | | |
| D | 0.05 | 0.15 | 0.002 | 0.006 | | |
| F | 0.50 | 0.75 | 0.020 | 0.030 | | |
| G | 0.65 | BSC | 0.026 | BSC | | |
| н | 0.50 | 0.60 | 0.020 | 0.024 | | |
| J | 0.09 | 0.20 | 0.004 | 0.008 | | |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 | | |
| K | 0.19 | 0.30 | 0.007 | 0.012 | | |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 | | |
| Г | 6.40 | | 0.252 BSC | | | |
| М | 0 ° | 8 ° | 0 ° | 8 ° | | |

SOLDERING FOOTPRINT



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